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ABSTRACT

PROCESS FOR REDUCING DISHING AND EROSION DURING CHEMICAL MECHANICAL PLANARIZATION

This invention is directed to a slurry system and process of metal removal from a substrate. This invention is useful for polishing a microelectronic device. This invention is especially useful for chemical mechanical planarization of a semiconductor wafer. The slurry system of the present invention includes a first slurry and a second slurry, wherein the first slurry has a higher abrasive concentration than the second slurry. The process of the present invention includes a first polish with the first slurry to partially remove metal from the substrate, and a second polish with the second slurry to further remove metal from the substrate.